ERRATA

Experimentally confirmed design guidelines for passively *Q*-switched microchip lasers using semiconductor saturable absorbers: errata

G. J. Spühler, R. Paschotta, R. Fluck, B. Braun, M. Moser, G. Zhang, E. Gini, and U. Keller

Ultrafast Laser Physics, Institute of Quantum Electronics, Swiss Federal Institute of Technology ETH Hönggerberg—HPT, CH-8093 Zürich, Switzerland

Received December 20, 2000

OCIS codes: 140.3480, 140.3540, 140.3580, 140.3530, 140.3500, 160.6000

We have detected the following error in our paper[1]: Fig. 5, which shows numerical solutions of the transcendental expression (A11), should be as shown below. The statements concluded from this graph still hold: As long as there are parasitic losses, optimized pulse energy is achieved for values of the total nonsaturable l close to $l \approx q_0$, and expressions (7) and (8) can be applied.

REFERENCE

1. G. J. Spühler, R. Paschotta, R. Fluck, B. Braun, M. Moser, G. Zhang, E. Gini, and U. Keller, "Experimentally confirmed design guidelines for passively Q-switched microchip lasers using semiconductor saturable absorbers," J. Opt. Soc. Am. B **16**, 376–388 (1999).

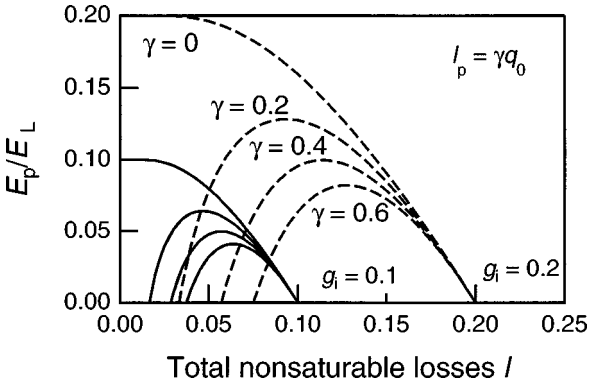

Fig. 5. Output pulse energy normalized to the saturation energy of the gain medium versus the total nonsaturable losses, for parasitic losses $l_p = \gamma q_0$ and two different fixed initial gains, obtained from the rate equations (A1)–(A3). The solid curves are plotted for the same values of γ as the dashed ones, but with lower initial gain. As soon as there are nonvanishing parasitic losses, maximum pulse energy is achieved for values of l close to $l \approx q_0 \approx g_i/2$.

0740-3224/2001/060886-01$15.00